3DA50

NPN Silicon High Frequency High Power Transistor

Features:

1. Excellent second breakdown capacity. Good characteristic frequency.
2. Amplification factor of small current is great. Good voltage resistance.
3. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
4. Use for analog computer power output, amplification of high frequency,middle frequency and low frequency, switching circuit.
5. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA: **(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications							Test Condition
			A	B	C	D	E	F	G	
Total Dissipation	P_{tot}	W	50							Tc:75°C
Max. Collector Current	I_{CM}	A	5							
Junction Temperature	T_{jm}	°C	175							
Storage Temperature	T_{stg}	°C	-55~+175							
C-B Breakdown Voltage	$V_{(BR)CBO}$	V	25	50	100	150	200	250	300	I_C=1mA
C-E Breakdown Voltage	$V_{(BR)CEO}$	V	25	50	100	150	200	250	300	I_C=1mA
E-B Breakdown Voltage	$V_{(BR)EBO}$	V	5							I_E=1mA
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	0.8							I_C=2.5A, I_B=0.5A
Collector-Base Leakage Current	I_{CBO}	mA	0.5							V_{CB}=20V
Collector-Emitter Leakage Current	I_{CEO}	mA	1.0							V_{CE}=20V
Base-Emitter Leakage Current	I_{BEO}	mA	2.0							V_{EB}=4V
DC Current Gain	h_{FE}		Red:15~25		Orange:25~40		Yellow:40~55			V_{CE}=5V, I_C=2.5A
			Green:55~80		Blue:80~120		Purple:120~180			
Transition frequency	f_T	MHz	30							V_{CE}=10V, I_C=0.5A f_O=10 MHz

Outline and Dimensions: